NSN 5961-01-081-0242

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Inclosure Material:

Ceramic

Overall Length:

Between 0.633 inches and 0.643 inches

Overall Height:

Between 0.125 inches and 0.135 inches

Overall Width:

Between 0.495 inches and 0.503 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Gate

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

80.0 breakdown voltage, collector-to-base, emitter open and 80.0 breakdown voltage, collector-to-emitter, base open and 5.0 breakdown

voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

Between 120.00 milliamperes source cutoff current and 8.00 amperes source cutoff current

Power Rating Per Characteristic:

2.2 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

100.0 degrees celsius junction

Special Features:

Junction pattern arrangement: pnp

Terminal Type And Quantity:

3 pin

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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